



■ FEATURES

- Accuracy 0.01% F.S.
- Measuring Pulse(TTL,CMOS), Magnetic pick-up
- Accepts input rates up to 50KHz
- Display type of RPM or line-speed can be modified
- Display unit M/min, Y/min,ft/min can be modified
- Input pulse of revolution can be modified (1~99999)
- Decimal point can be modified
- Dimension small and High stability

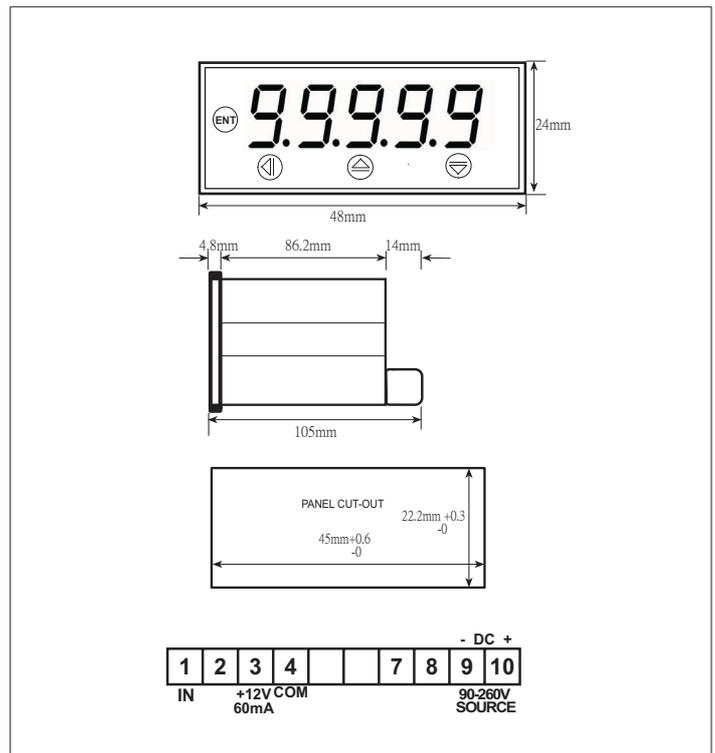
1.MODEL:MRS-□ □ □

NO	Input Type	NO	Display unit	NO	Aux.Power
A	Pulse (TTL) (5V)	1	RPM	A	AC/DC18~60V
B	Pulse (NPN) (12V)	2	M/min	B	AC/DC90~260V
C	Pulse (PNP) (12V)	3	Y/min	• LESS 3VA for AC/DC input	
D	Magnetic pick-up(50mV~1.5V)	4	f t/min		
E	Magnetic pick-up(500mV~15V)	9	SPECIFIED		
F	AC2~60V				
O	SPECIFIED				

2.SPECIFICATION

- Measuring accuracy : 0.01% F.S. (23±5°C)
- Count input type : Jump-pin selectable current sourcing(NPN) or current sinking (PNP)
- Count input trigger levels : Hi bias (CMOS) (V<sub>IH</sub>=7.5V, V<sub>IL</sub>=5.5V)  
Lo bias (TTL) (V<sub>IH</sub>=3.7V, V<sub>IL</sub>=2.0V)
- Max.count rates : 50KHz (50% duty cycle)
- Sampling time : 10 cycles/sec. (>10Hz)  
f cycles/sec. (<10Hz)
- Over input indication : " doFL "
- Readout range : 0~99999 digit adjustable
- Diameter setting : 0~9.9999M (Touch switches setting)
- Parameter setting : Touch switches
- Display : Red high efficiency LEDs high 10.16mm (0.4")
- Sensor power supply : 12VDC±3%(<60mA)
- Memory mode : Non-volatile E<sup>2</sup> PROM memory
- Dielectric strength : 2KVac/1 min. (input/power/display)
- Operating condition : 0~50°C (20 to 90% RH non-condensed)
- Storage condition : 0~70°C (20 to 90% RH non-condensed)
- CE EMC Certification : EN 55022:1998/A1:2000 Class A  
EN 61000-3-2:2000  
EN 61000-3-3:1995/A1:2001  
EN 55024:1998/A1:2001

3.OUTSIDE DIMENSION AND CONNECTION DIAGRAM



4.Ordering information

MODEL:MRS-B1B

- Input Type : Pulse (NPN) (12V)
- Display unit : RPM
- Aux. power supper : AC/DC90~260V